Unit: mm

TOSHIBA Transistor Silicon NPN Triple Diffused Type (PCT process)

2SC5172

Switching Regulator and High-Voltage Switching Applications

High-Speed DC-DC Converter Applications

• Excellent switching times: $t_r = 0.5 \mu s$ (max),

 $t_f = 0.3 \mu s \text{ (max) at IC} = 2 \text{ A}$

• High collector breakdown voltage: $V_{CEO} = 400 \text{ V}$

Absolute Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	600	٧	
Collector-emitter voltage		V _{CEO}	400	V	
Emitter-base voltage		V _{EBO}	7	V	
Collector current	DC	Ic	5	Α	
	Pulse	ICP	7		
Base current		I _B	2	Α	
Collector power dissipation	Ta = 25°C	D-	2.0	W	
	Tc = 25°C	P _C	25		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

1. BASE 2. COLLECTOR 3. EMITTER

JEDEC

JEITA

SC-67

TOSHIBA

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Weight: 1.7 g (typ.)

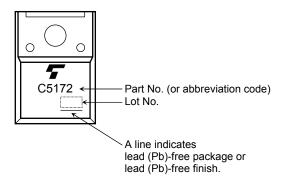
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

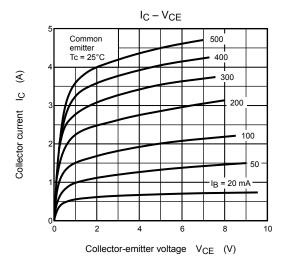
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

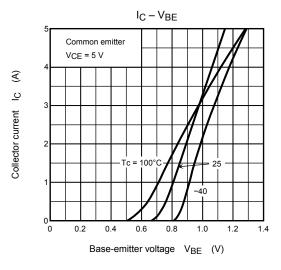
Electrical Characteristics (Tc = 25°C)

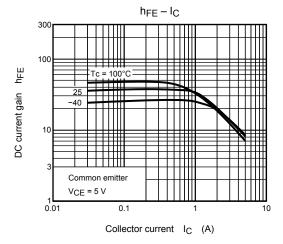
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off of	urrent	I _{CBO}	V _{CB} = 500 V, I _E = 0	_	_	20	μΑ
Emitter cut-off cui	rrent	I _{EBO}	V _{EB} = 7 V, I _C = 0	_	_	100	nA
Collector-base breakdown voltage		V (BR) CBO	I _C = 1 mA, I _E = 0	600	_	_	V
Collector-emitter breakdown voltage		V (BR) CEO	I _C = 10 mA, I _B = 0	400	_	_	V
DC current gain		h _{FE (1)}	V _{CE} = 5 V, I _C = 1 mA	13	_	_	
		h _{FE (2)}	V _{CE} = 5 V, I _C = 0.5 A	20	_	65	
Collector-emitter saturation voltage		V _{CE} (sat)	I _C = 2 A, I _B = 0.25 A	_	_	1.0	V
Base-emitter saturation voltage		V _{BE (sat)}	I _C = 2 A, I _B = 0.25 A	_	_	1.3	٧
Switching time Storage time Fall time	Rise time	t _r	Output 20 μ s Input $\downarrow B_1$ $\downarrow C$		_	0.5	
	Storage time	t _{stg}		ı	_	2.0	μs
	Fall time	t _f			_	0.3	

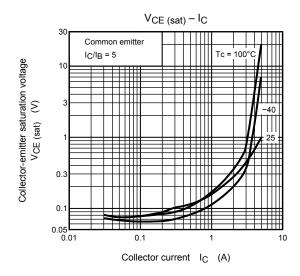
Marking

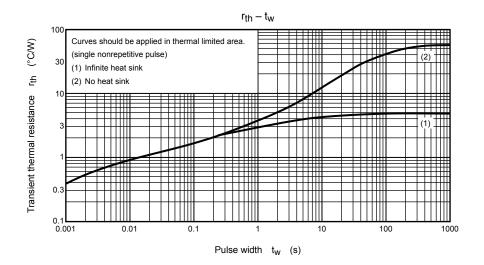


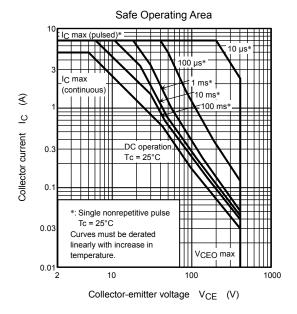












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